



### **Product Summary**

BV <sub>DSS</sub>	R <sub>ds(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
60V	$0.04\Omega$ @ V <sub>GS</sub> = 10V	7.5A
	$0.06\Omega @ V_{GS} = 4.5V$	6.2A

# Description

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

# Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

### 60V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Voltage
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

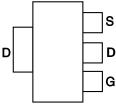
# **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Weight: 0.112 grams (Approximate)

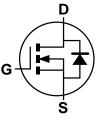


**SOT223** 

Top View



Pin Out - Top View



Equivalent Circuit

# Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMN6A09GTA	SOT223	1,000/ Tape & Reel

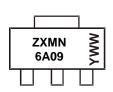
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



SOT223

ZXMN6A09 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 9 = 2019) WW = Week Code (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current $@V_{GS} = 10V; T_A = +25^{\circ}C$ (Note 6)		7.5	
@V <sub>GS</sub> = 10V; T <sub>A</sub> = +70°C (Note 6)	I <sub>D</sub>	6	A
@V <sub>GS</sub> = 10V; T <sub>A</sub> = +25°C (Note 5)		5.4	
Pulsed Drain Current (Note 7)	IDM	33	A
Continuous Source Current (Body Diode) (Note 6)	I <sub>S</sub>	3.5	A
Pulsed Source Current (Body Diode) (Note 7)	I <sub>SM</sub>	33	A
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	1.17	A
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	0.07	mJ

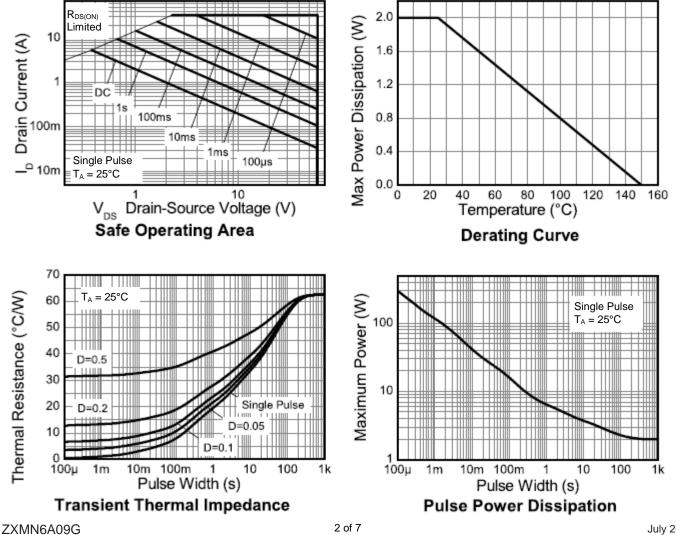
# **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	PD	2.0 16	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear Derating Factor	PD	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	32.2	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C
Notes: 5. For a device surface mounted on 25mm × 25mm FR-4 PCE		d 1oz copper. in still air conditi	ons.

5. For a device surface mounted on 25mm × 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.

6. For a device surface mounted on FR-4 PCB measured at t  $\leq$  10s.

7. Repetitive rating 25mm × 25mm FR-4 PCB, D = 0.02 pulse width = 300 µs - pulse width limited by maximum junction temperature.





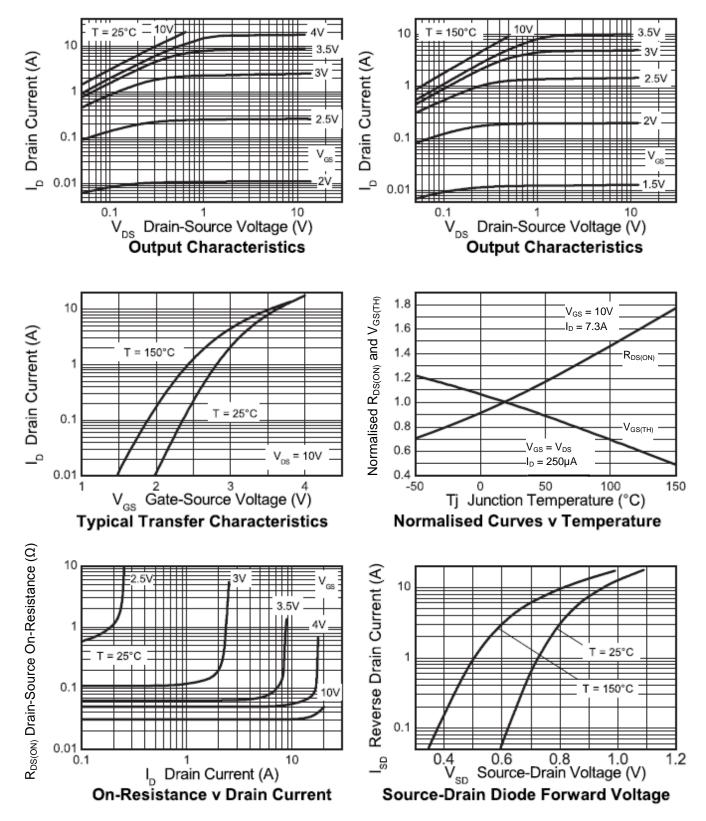
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	—	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	—	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)	Р	—	0.02	0.04	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 8.2A	
	R <sub>DS(ON)</sub>		0.03	0.06	Ω	$V_{GS} = 4.5V, I_D = 7.4A$	
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	_	0.85	0.95	V	$I_{S} = 6.6A, V_{GS} = 0V, T_{J} = +25^{\circ}C$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 10)	Ciss	_	1407	—	pF		
Output Capacitance (Note 10)	Coss	—	121	—	pF	$V_{DS} = 40V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance (Note 10)	C <sub>rss</sub>	_	59	—	pF		
Total Gate Charge (Notes 9 &10) $V_{GS} = 5V$	Qg	_	12.4	—	nC	V <sub>DS</sub> = 15V I <sub>D</sub> = 3.5A	
Total Gate Charge (Notes 9 &10) $V_{GS} = 10V$	Qg	_	24.2	—	nC		
Gate-Source Charge (Notes 9 &10)	Q <sub>gs</sub>	_	5.2	—	nC		
Gate-Drain Charge (Notes 9 &10)	Q <sub>gd</sub>	_	3.5	—	nC		
Turn-On Delay Time (Notes 9 & 10)	t <sub>D(ON)</sub>	_	4.9	—	ns	V <sub>DD</sub> = 15V, I <sub>D</sub> = 3.5A, V <sub>GS</sub> = 5V	
Turn-On Rise Time (Notes 9 & 10)	t <sub>R</sub>	_	5.0	—	ns		
Turn-Off Delay Time (Notes 9 & 10)	t <sub>D(OFF)</sub>	_	25.3	—	ns		
Turn-Off Fall Time (Notes 9 & 10)	t <sub>F</sub>	_	4.6	_	ns		
Reverse Recovery Time (Note 10)	t <sub>RR</sub>		26.3		ns	I <sub>F</sub> = 3.5A, di/dt = 100A/μs,	
Reverse Recovery Charge (Note 10)	Q <sub>RR</sub>		26.6	—	nC	$T_{\rm J}$ = +25°C	

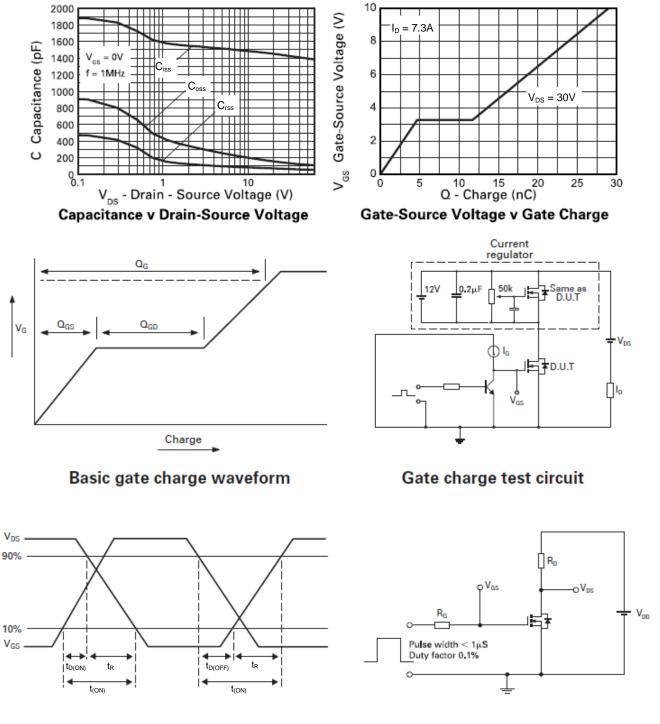
 Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
Switching characteristics are independent of operating junction temperature.
For design aid only, not subject to production testing. Notes:



# ZXMN6A09G







Switching time waveforms

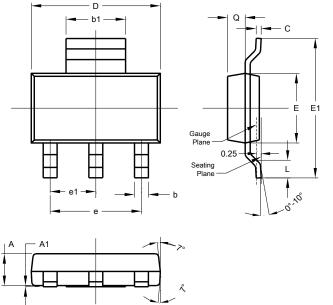
Switching time test circuit



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

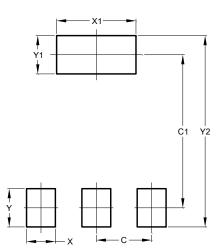
**SOT223** 



	SOT223				
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All I	All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223

Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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